By 2024, worldwide data volume is expected to reach 143 zettabytes (source IDC/three.numr)

KIOXIA Makes Data Work – Innovation in Action

1st to Introduce Commercial 1Gb MLC NAND

World’s 1st 3D Flash Memory Technology Announced

World’s first UFS Introduced

World’s 1st 15nm 128Gb NAND Flash Memory Introduced

World’s 1st 48-layer 3D Flash Memory

1st to Introduce 4-bit-per-cell Technology (QLC BiCS FLASH 3D Flash Memory)

Achieved Industry’s Highest Capacity of 1.33 Terabits for a single chip (QLC BiCS FLASH)

1st to Sample UFS Version 3.0

Introduced 112-Layer 3D Flash Memory Technology

“Changing the world through innovative solutions.”

Nobuo Hayasaka
President and CEO, KIOXIA Corporation

THE INVENTOR OF FLASH MEMORY

A Legacy of Innovation
KIOXIA delivers flash-based products for next generation storage applications. With a steadfast commitment to technology innovation, KIOXIA will continue to push the boundaries of what’s possible.

INNOVATION STARTS WITH KIOXIA

1987 Invented NAND Flash Memory

1991 World’s 1st Mass Production of NAND Flash Memory

2001 1st to Introduce Commercial 1Gb MLC NAND

2007 World’s 1st 3D Flash Memory Technology Announced

2013 World’s first UFS Introduced

2014 World’s 1st 15nm 128Gb NAND Flash Memory Introduced

2015 World’s 1st 48-layer 3D Flash Memory

2017 1st to Introduce 4-bit-per-cell Technology (QLC BiCS FLASH 3D Flash Memory)

2018 Mass Production of 96-layer 3D Flash Memory

2019 1st to Sample UFS Version 3.0

2020 Introduced 112-Layer 3D Flash Memory Technology

KIOXIA America, Inc. (formerly Toshiba Memory America, Inc.) is headquartered in Sunnyvale, California. (Supporting press releases available upon request.

2) IDC Worldwide Global DataSphere Forecast, 2020–2024, April 2020, Doc # US44797920

1) KIOXIA America, Inc. (formerly Toshiba Memory America, Inc.)